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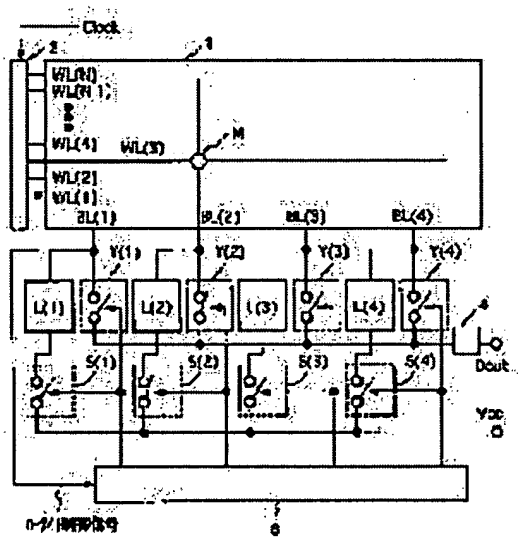
(54) SEQUENTIAL READING MEMORY

(57)Abstract:
PROBLEM TO BE SOLVED: To control the load resistance of a bit line and to greatly reduce the power consumption by pulling up only the selected bit line by the load resistance and providing the means which separates a anon-selected bit line from a power supply.
SOLUTION: When a word line WL (3) and a bit line BL (2) are selected, a conventional switch S (2) is controlled in a conductive condition and signal voltages corresponding to the stored contents appear across a load resistor L (2). By detecting the voltages by a reading circuit 4, the stored contents are read to the external. However, in the embodiment, remaining switches S (1), S (3) and S (4) are controlled into a non-conductive state, no current flows into a memory cell from a power supply Vcc through load resistors L (1), L (3) and L(4). Thus, the power corresponding to the current is reduced.



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